OPTIMISED BCD ADDER CIRCUIT DESIGN USING RATE SENSING KEEPER

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ABSTRACT:
The basic factors which affect any VLSI circuit design are area, speed and power consumption. Full adder is a basic element used in multiplexers, processor designs. Full adders can be implemented using CMOS technology. The CMOS technology plays a major role on the performance of microprocessors on very large scale integrated circuits chips. In this paper Full adder circuit is designed based on conventional domino logic using "Rate sensing keeper" technique. This technique helps to achieve high speed, low noise than conventional CMOS. The full adder circuit design using "Rate Sensing Keeper" gives superior performance compared to Full adder circuits designed using other techniques. In this finally implement BCD adder by using Full adder circuit is designed based on conventional domino logic with "Rate sensing keeper" technique. on mentor graphics tool 130 nm technology.

Keywords: CMOS, Domino logic, Rate sensing keeper technique, scaling technology

I.INTRODUCTION
CMOS technology plays a major role on the performance of VLSI circuits. The timing performance of the microprocessor can be improved by using dynamic circuits in microprocessors. However the usage of dynamic circuits in microprocessors is limited due to many challenges including transistor sizing, charge sharing, leakage current, noise immunity etc. Timing optimization of dynamic circuits can be achieved through several methods such as transistor sizing, using multiple threshold voltages etc.. The aggressive scaling of transistors and interconnect dimensions has caused noise to become an increasingly important issue in integrated circuit design. A number of design techniques have been proposed to enhance the noise tolerance of domino logic circuit. The delay of the dynamic circuits can be controlled by varying the sizes of transistors in the circuit. The circuit delay can be reduced by increasing the transistor sizes in the circuit. This means that high speed circuits require larger area. So for dynamic circuits, there is a trade off exist between speed and area. Domino logic circuits are the most widely used dynamic logic style. Domino logic circuits have two phases of operations-first phase called precharge phase and second phase called evaluation phase. During the precharge phase of the domino logic circuits, the clock remains low and the dynamic node is precharged to V DD through a p-type pull up transistor. The evaluation phase starts when the clock transit from low to high and during this phase the pull down network evaluates the logic function.

The important considerations in domino circuit design technique are charge sharing, leakage current, noise immunity and reliability. To improve the reliability and performance of domino logic circuits, a number of circuit techniques have been developed in the past three decades such as: 1) using a simple keeper 2) precharging the internal nodes 3) raising the source voltage 4) leakage current replica technique 5) conditional keeper technique 6) current comparison domino method etc. A domino logic circuit is inherently susceptible to noise due to floating nodes that may occur in the evaluation phase. In this paper a full adder circuit is designed and simulated using Rate sensing keeper technique which improves the timing and noise tolerance of the full adder circuit compared to other full adder circuits. The rate sensing keeper (RSK) technique based full adder circuit work based on the difference in the rate of change of voltage at the dynamic node of the gate during the ON and the leakage condition. The state of the keeper is controlled by a reference rate which is the average of...
the rate of change of voltage at the dynamic node of the gate during the ON and the leakage condition. One method to reduce the sub threshold leakage current in domino circuits is the usage of diode footer. The diode footer reduces the sub threshold leakage current in the domino circuit due to a phenomenon called the stacking effect. A voltage drop will be established across the diode footer in the evaluation phase due to the leakage of the evaluation transistors in the pull down network.

The paper is organized as follows. Section II Existed method full adder and Section III operation of the full adder using RSK technique. Section IV Simulation result and Section V Conclusion

II EXISTED METHOD FULL ADDER

In which, the full adder is implemented based on domino logic technique. The basic logic diagram of domino logic is shown in below fig (a)

![Fig(a) basic logic diagram of domino logic](image)

The above fig(a) shows the basic domino logic inverter diagram that operate in two modes one is precharged which is occur when clock is low and another one is evaluation which is occur when clock is low. The below fig (b)&(c) shows the domino logic based sum and carry MENTORGRAPHICS TOOLS 130 nm technology

![fig(b): the domino logic based sum](image)

![Fig(c): the domino logic based sum](image)

It provides low power dissipation than CMOS but add noise in the result. Hence in order to control that, in this paper modified the above adder with rate sensing keeper technique shown in below proposed method
III PROPOSED METHOD FULL ADDER

In order to overcome the noise and leakage power in the above existed domino logic and achieve the high speed, for that modified the above circuit with rate sensing keeper technique shown in below fig. this proposed method gives the better performance compared to all existed methods.
The Domino logic with Rate sensing keeper technique based full adder is shown in below implemented based on MENTORGRAPHICS TOOLS 130 nm technology

![Domino logic with Rate sensing keeper technique based full adder](image)

**BCD ADDER IMPLEMENTATION**

Finally, we selected Domino logic with Rate sensing keeper technique based full adder, based on that in which, we were implemented 4-Bit BCD adder shown in below fig

![4-Bit BCD adder](image)

For implementation of the above circuit, used two 4-bit binary adders and two AND, one OR gates. The implementation of 4-bit binary adder is shown in below fig
IV SIMULATION RESULT

The simulations are performed based on mentor graphics tools with 130nm technology. The below fig(a)&(b) shows the resultant wave forms of domino logic based full adder sum and carry.

From the above fig we observed that, added noise in output sum and carry waveforms. Hence in order to overcome that, we were proposed and modifier above method with rate sensing keeper shown in below fig(c) and (d), that shows the resultant wave forms of domino logic with Rate sensing keeper based full adder sum and carry.
From the above fig(c) & (d) we observed that, reduced noise in output sum and carry waveforms compared to fig(c) and (d). The output noise decreases with increase in bias voltage. But the increase in bias voltage also increases the circuit delay. So the selection of bias voltage plays a major role in the circuit operation. The full adder circuit implemented based on an adaptive keeper technique called rate sensing keeper (RSK) that enables faster switching and the experimental results shows that the full adder circuit designed using rate sensing keeper transistor technique gives superior performance compared to the other alternatives.

V CONCLUSION

In this paper the performance of a full adder circuit designed using rate sensing keeper transistor technique is analyzed in detail and its performance is compared with other full adder circuits. The full adder circuit is simulated using MENTORGRAPHICS TOOLS on 130nm. The experimental results shows that the full adder circuit designed using rate sensing keeper transistor technique gives superior performance compared to full adder circuits designed using conventional domino techniques. The performance of the wide fan in circuits implemented using domino logic technologies can be further improved by using Fin FET devices. Another advantage of using Fin FET is its high scalability and low leakage power compared to conventional MOSFETs.

REFERENCES


